

etching the first mask pattern by an isotropic dry etching so as to form a second mask pattern, wherein the isotropic dry etching is carried out with plasma dry etching equipment, which uses a microwave energy source;

removing the insulating layer by a first anisotropic dry etching using the second mask pattern;

removing the second mask pattern; and

etching the conducting layer by a second anisotropic dry etching using the remaining insulating layer, so as to form the bit line.

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5. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out while oxygen gas is supplied.

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9. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out using a source of power of less than 400 Watts.

10. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out using a source of power of 200 to 300 Watts.

11. (Amended) The method as claimed in claim 1, wherein the isotropic dry etching is carried out using a pressure of 600 to 1000 mT.

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Please add the following claim:

--15. (New) A method of manufacturing a bit line having a width of not more than 0.1  $\mu\text{m}$ , the method comprising the steps of:

- successively forming a conducting layer and an insulating layer on a substrate;
- forming a photoresist film on the insulating layer;
- patterning the photoresist film using a photolithography process such that a desired region of the insulating layer is exposed to form a first photoresist pattern having a width of at least 0.14  $\mu\text{m}$ ;
- partially removing the first photoresist pattern by an isotropic dry etching process so as to form a second photoresist pattern having a width of not more than 0.1  $\mu\text{m}$ , said isotropic dry etching process being carried out by supplying oxygen gas at a flow rate of approximately 800 sccm, using a microwave energy source having a power less than 400 Watts and at a pressure of approximately 600 to 1,000 mT;
- removing a portion of said insulating layer by a first anisotropic dry etching using the second photoresist pattern as a mask, a remaining portion of said insulating layer forming a hard mask;
- removing the second photoresist pattern; and
- etching the conducting layer by a second anisotropic dry etching using the hard mask so as to form the bit line, said bit line having a same shape as said second photoresist pattern such that said bit line has a width of not more than 0.1  $\mu\text{m}$ .--